

**Application No. 09/502,729**

Dielectric insulation layer with uniformly distributed nitride layer

East Search						8/8/01
Search	L No.	Hits	Text Search			Data Bases
IS&R	L1	9265	("257/40,77,288,296,321,324,325,327,350,368,374,410,501,506,507,508,520,524,635,636,639,640,643,646,647,649,709").CCLS.		8/8/01 9:51	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L2	7310	1 and (layer layering barrier)		8/8/01 9:55	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L3	3560	2 and (si02 sin sic sich (silicon adj oxide) (silicon adj nitride) (silicon adj carbide))		8/8/01 9:57	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L4	1936	3 and dielectric		8/8/01 9:58	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L5	461	4 and (non-uniform\$3 nonuniform\$3 mixture (random\$2 adj distribut\$3))		8/8/01 10:00	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L6	49	5 and (diffusion adj barrier)		8/8/01 10:00	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB

**Search Result**

USPAT	Date	Page	Title	CI/Sub	CI/Sub	Inventor
US 5726497 A	19980310	8	Upward plug filled via hole device	257/758	257/751 ; 257/915 ; 428/332 ; 428/650 ; 428/660 ; 428/688 ; 428/704	Chao, Ying-Chen , et al.
US 5818071 A	19981006	5	Silicon carbide metal diffusion barrier layer	257/77	257/55 ; 257/63	Loboda, Mark Jon , et al.
US 5825046 A	19981020	12	Composite memory material comprising a mixture of phase-change memory material and dielectric material	257/2	257/4 ; 257/5 ; 257/77 ; 365/163	Czubatyj, Wolodymyr . et al.
US 5856705 A	19990105	15	Sealed semiconductor chip and process for fabricating sealed semiconductor chip	257/758	257/640 ; 257/641 ; 257/760 ; 257/786	Ting, Chiu H.
US 5949143 A	19990907	7	Semiconductor interconnect structure with air gap for reducing intralayer capacitance in metal layers in damascene metalization process	257/758	257/522	Bang, David
US 6008540 A	19991228	24	Integrated circuit dielectric and method	257/758	257/3 ; 257/642	Lu, Jiong-Ping , et al.
US 6133144 A	20001017	11	Self aligned dual damascene process and structure with low parasitic capacitance	438/634	257/758 ; 257/760 ; 257/761 ; 257/776 ; 438/618 ; 438/622 ; 438/624 ; 438/638	Tsai, Ming-Hsing , et al.
US 6208016 B1	20010327	12	Forming submicron integrated-circuit wiring from gold, silver, copper and other metals	257/643	257/642 ; 257/751 ; 257/759 ; 257/761 ; 257/762	Farrar, Paul A.
US 6239494 B1	20010529	6	Wire bonding CU interconnects	257/762	257/700 ; 257/736 ; 257/748 ; 257/750 ; 257/758 ; 257/764 ; 257/765 ; 257/771	Besser, Paul R. , et al.
US 6249055 B1	20010619	12	Self-encapsulated copper metallization	257/758	257/751 ; 257/752 ; 257/762 ; 257/765	Dubin, Valery

US 6255731 B1	20010703	25	SOI bonding structure	257/758	257/751 ; 257/757 ; 257/759 ; 257/768 ; 257/769 ; 257/772	Ohmi, Tadahiro , et al.
US 6265740 B1	20010724	8	Semiconductor device capacitor using a fill layer and a node on an inner surface of an opening	257/296	257/297 ; 257/298 ; 257/300 ; 257/303 ; 257/305 ; 257/309 ; 257/310 ; 257/311 ; 361/303 ; 361/306.3 ; 361/311	Kim, Jin-won
US 6265779 B1	20010724	17	Method and material for integration of fluorine-containing low-k dielectrics	257/759	257/762 ; 257/763 ; 438/623 ; 438/624 ; 438/643 ; 438/644	Grill, Alfred , et al.
US 6271593 B1	20010807	13	Method for fabricating conductive components in microelectronic devices and substrate structures therefor	257/752	257/637 ; 257/640 ; 257/758 ; 257/760	Givens, John H. , et al.

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	351	(diffusion adj barrier) and nitrid\$6 and silicon and hydrogen and carbon	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/09 11:54
2	BRS	L2	5	1 and organosilane	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/09 12:01
3	BRS	L3	41	1 and densif\$5	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/09 12:02
4	BRS	L4	41	1 and densif\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/09 12:02